

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Canceled).

Claim 6 (Currently Amended): ~~The A manufacturing method of a nonvolatile semiconductor memory device, according to claim 5 comprising:~~

making element isolation/insulation films that partition element-forming regions in a semiconductor substrate;

stacking a first gate electrode material film and a second gate insulating film on said semiconductor substrate via a first gate insulating film;

etching said second gate insulating film and the underlying first gate electrode material film to make slits that separate said first gate electrode material film above said element isolation/insulation films;

forming an insulating film on side surfaces of said first gate electrode material film,
and thereafter stacking a second gate electrode material film;

sequentially etching said second gate electrode material film, said second gate insulating film, and said first gate electrode material film to pattern said first gate electrode material film into floating gates and said second gate electrode material film into control gates; and

making source and drain diffusion layers in self alignment with said control gates;
wherein said first gate electrode material film is a multi-layered film including a first conductive film stacked before formation of said element isolation/insulation films and a second conductive film stacked after formation of said element isolation/insulation film films.

Claims 7-8 (Canceled).

Claim 9 (Previously Presented): The manufacturing of a nonvolatile semiconductor memory device according to claim 6 wherein said element isolation/insulation films are buried in grooves formed into said semiconductor substrate.

Claim 10 (Original): The manufacturing of a nonvolatile semiconductor memory device according to claim 6 wherein said second gate insulating film is a multi-layered film including silicon oxide film / silicon nitride film / silicon oxide film.

Claims 11-13 (Canceled).

Claim 14 (New): A method for manufacturing a nonvolatile semiconductor memory device, comprising:

forming a first insulating film on a semiconductor substrate having a first upper surface;

forming a first electrode material film on the first insulating film, the first electrode material film having a second upper surface;

etching the first electrode material film, the first insulating film, and the semiconductor substrate so as to form an element isolation groove in the semiconductor substrate;

embedding a second insulating film in the element isolation groove and forming an isolation portion so that a third upper surface of the isolation portion protrudes from the first upper surface and a height of the third upper surface from the first upper surface is lower than a height of a second upper surface from the first upper surface;

forming a second electrode material film on the first electrode material and the second insulating film;

forming a third insulating film on the second electrode material;

etching the third insulating film and the second electrode material film and forming a slit on the second insulating film so that the second electrode material film is separated on the second insulating film;

forming a fourth insulating film on an inner side wall of the slit; and

forming a third electrode material film on the third insulating film and in the slit.

Claim 15 (New): The method for manufacturing a nonvolatile semiconductor memory device according to claim 14, wherein the third insulating film has two silicon oxide films and a silicon nitride film located between the silicon oxide films.

Claim 16 (New): The method for manufacturing a nonvolatile semiconductor memory device according to claim 14, wherein the fourth insulating film has a silicon oxide film.